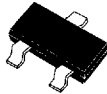


CMPD2003
CMPD2004
CMPD2004S

HIGH VOLTAGE SWITCHING DIODE



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD2003, CMPD2004, CMPD2004S types are silicon switching diodes manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

The following configurations are available:

CMPD2003	SINGLE
CMPD2004	SINGLE
CMPD2004S	DUAL, IN SERIES

MARKING CODE: A82
MARKING CODE: D53
MARKING CODE: DB6

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	CMPD2003	CMPD2004 CMPD2004S	UNITS
Continuous Reverse Voltage	V _R	200	240	V
Peak Repetitive Reverse Voltage	V _{RRM}	250	300	V
Peak Repetitive Reverse Current	I _O	200	200	mA
Continuous Forward Current	I _F	250	225	mA
Peak Repetitive Forward Current	I _{FRM}	625	625	mA
Forward Surge Current, tp=1 μs	I _{FSM}	4000	4000	mA
Forward Surge Current, tp=1 s	I _{FSM}	1000	1000	mA
Power Dissipation	P _D		350	mW
Operating and Storage				
Junction Temperature	T _J , T _{stg}	-65 to +150		°C
Thermal Resistance	θ _{JA}	357		°C/W

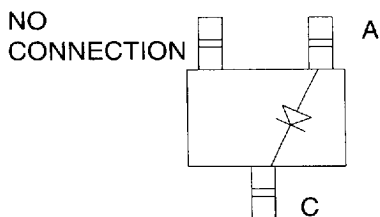
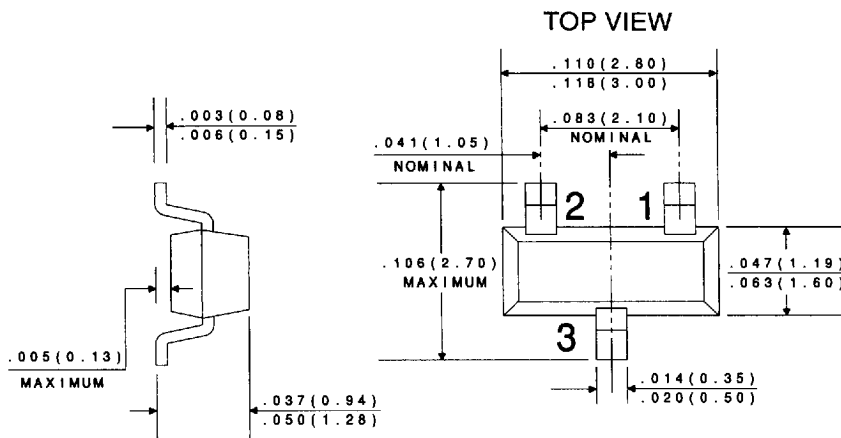
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPD2003		CMPD2004 CMPD2004S		UNIT
		MIN	MAX	MIN	MAX	
B _{VR}	I _R =100 μA	250		300		V
I _R	V _R =200V		100		-	nA
I _R	V _R =200V, T _A =150°C		100		-	μA
I _R	V _R =240V		-		100	nA
I _R	V _R =240V, T _A =150°C		-		100	μA
V _F	I _F =100mA		1.0		1.0	V

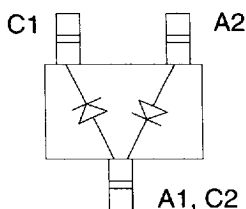
1989963 0001783 251 132

SYMBOL	TEST CONDITIONS	CMPD2003		CMPD2004 CMPD2004S		UNIT
		MIN	MAX	MIN	MAX	
V_F	$I_F=200\text{mA}$		1.25		-	V
C_T	$V_R=0$, $f=1\text{ MHz}$		5.0		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}$, RECOV. TO 3.0mA , $R_L=100\Omega$		50		50	ns

All dimensions in inches (mm).



**CMPD2003
CMPD2004**



CMPD2004S

DATA
SHEET

R2

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